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4.2 Creation of Porous GaN by Electroless Etching
4.3 Morphology Characterization; 4.3.1 Porous GaN Derived from Unintentionally Doped Films; 4.3.2 Transmission Electron Microscopy (TEM) Characterization; 4.4 Luminescence of Porous GaN; 4.4.1 Cathodoluminescence (CL) of Porous GaN; 4.4.2 Photoluminescence (PL) of Porous GaN; 4.5 Raman Spectroscopy of Porous GaN; 4.5.1 Characteristics of Raman scattering in GaN; 4.5.2 Raman Spectra of Porous GaN Excited Below Band Gap; 4.6 Summary and Conclusions; Acknowledgements; References; 5 Growth of GaN on Porous SiC by Molecular Beam Epitaxy
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7.2.3 Monitoring of Anodization Process

Sommario/riassunto

Porous Silicon Carbide and Gallium Nitride: Epitaxy, Catalysis, and Biotechnology Applications presents the state-of-the-art in knowledge and applications of porous semiconductor materials having a wide band gap. This comprehensive reference begins with an overview of porous wide-band-gap technology, and describes the underlying scientific basis for each application area. Additional chapters cover preparation, characterization, and topography; processing porous SiC; medical applications; magnetic ion behavior, and many more
